To our customers,

Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

Send any inquiries to http://www.renesas.com/inquiry.

RENESAS

RENESAS

SILICON POWER TRANSISTOR
NTC1863

HIGH SPEED HIGH CURRENT SWITCHING
NPN SILICON EPITAXIAL MESA TRANSISTOR

Industrial Use

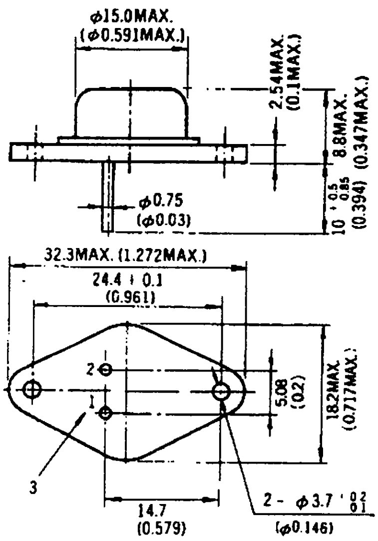
DESCRIPTION

Suitable for switching regulator, DC-DC converter and ultrasonic appliance applications.

FEATURES

- High speed switching.
- Low collector saturation voltage.
- Specified of reverse biased S.O.A. with inductive loads.

PACKAGE DIMENSIONS
in millimeters (inches)



1. Base
2. Emitter
3. Collector (Case)

EIAJ :TC-16,TB-23
JEDEC:TO-66
IEC :C13

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents (Ta = 25°C)			
Collector to Emitter Voltage	V_{CEX}	150	V
Collector to Emitter Sustaining Voltage	$V_{CEO(SUS)}$	100	V
Collector to Emitter Sustaining Voltage	$V_{CEX(SUS)}$	150	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Continuous Collector Current	$I_{C(DC)}$	7.0	A
Peak Collector Current*	$I_{C(pulse)}$	15	A
Continuous Base Current	$I_{B(DC)}$	4.0	A
Peak Base Current*	$I_{B(pulse)}$	8.0	A
Maximum Power Dissipations			
Total Power Dissipation	$P_{T(Tc=25°C)}$	50	W
Total Power Dissipation	$P_{T(Tc=100°C)}$	29	W
Total Power Dissipation	$P_{T(Ta=25°C)}$	2.0	W
Maximum Temperatures			
Junction Temperature	T_j	200	°C
Storage Temperature	T_{stg}	-65 to +200	°C
Lead Temperature 1/8 inch from case for 10 seconds	T_L	260	°C
Thermal Resistances			
Junction to Case	$R_{th(j-c)}$	3.50	°C/W
Junction to Ambient	$R_{th(j-a)}$	87.5	°C/W

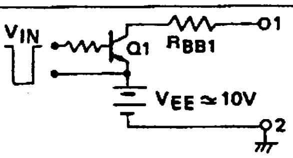
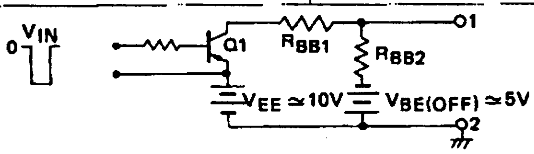
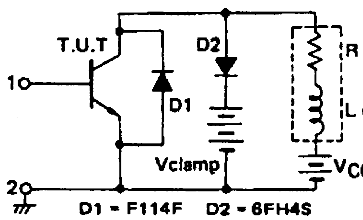
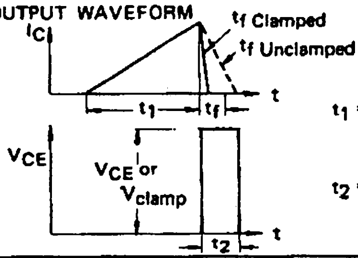
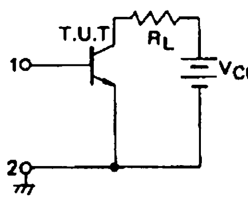
* Pulsed PW ≦ 300 μs, duty cycle ≦ 10%

ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector to Emitter Sustaining Voltage	$V_{CEO(SUS)}$	100			V	Table 1. I_C = 5A, I_{B1} = 0.5A, L = 100μH
	$V_{CEX(SUS)1}$	150			V	Table 1. I_C = 5A, I_{B1} = $-I_{B2}$ = 0.5A V_{clamp} = Rated V_{CEX}, Ta = 125°C
	$V_{CEX(SUS)2}$	100			V	Table 1. I_C = 10A, I_{B1} = 1.0A, I_{B2} = −0.5A V_{clamp} = Rated V_{CEX}, Ta = 125°C
Collector Cutoff Current	I_{CER}			1.0	mA	V_{CE} = 150V, R_{BE} = 50Ω, Ta = 125°C
	I_{CEX}			100	μA	V_{CE} = 150V, $V_{BE(OFF)}$ = −1.5V
	I_{CEX}			500	μA	V_{CE} = 150V, $V_{BE(OFF)}$ = −1.5V Ta = 125°C
Emitter Cutoff Current	I_{EBO}			10	μA	V_{EB} = 7.0V, I_C = 0
Second Breakdown Collector Current	$I_{S/B}$	2.5			A	t = 1.0 s, V_{CE} = 20V, Tc = 25°C
Second Breakdown Energy	$E_{S/B}$	500			μJ	I_C = 5A, I_{B1} = 0.5A, $V_{BE(OFF)}$ = −5V
DC Current Gain	h_{FE1}	20		160		V_{CE} = 5V, I_C = 3A **
	h_{FE2}	15				V_{CE} = 5V, I_C = 5A **
Collector Saturation Voltage	$V_{CE(sat)}$			1.0	V	I_C = 5A, I_B = 0.5A **
	$V_{CE(sat)}$			1.5	V	I_C = 5A, I_B = 0.5A, Ta = 125°C **
Base Saturation Voltage	$V_{BE(sat)}$			1.5	V	I_C = 5A, I_B = 0.5A **
	$V_{BE(sat)}$			1.5	V	I_C = 7A, I_B = 0.7A, Ta = 125°C **
Gain Bandwidth Product	f_T	20			MHz	V_{CE}=10V, I_C=50mA, f_o=3.0MHz, Tc=25°C
Output Capacitance	C_{ob}			300	pF	V_{CB} = 10V, f_o = 1.0 MHz
Delay Time	t_d			0.1	μs	Resistive Load (Table 1.)
Rise Time	t_r			0.7	μs	
	t_r			2.1	μs	Ta = 125°C I_C = 5A, I_{B1} = $-I_{B2}$ = 0.5A
Storage Time	t_{stg}			1.0	μs	R_L = 10Ω, V_{CC} ≃ 50V
	t_{stg}			1.5	μs	Ta = 125°C PW ≃ 50μs, duty cycle ≦ 2%
Fall Time	t_f			3.0	μs	
	t_f			1.2	μs	Ta = 125°C

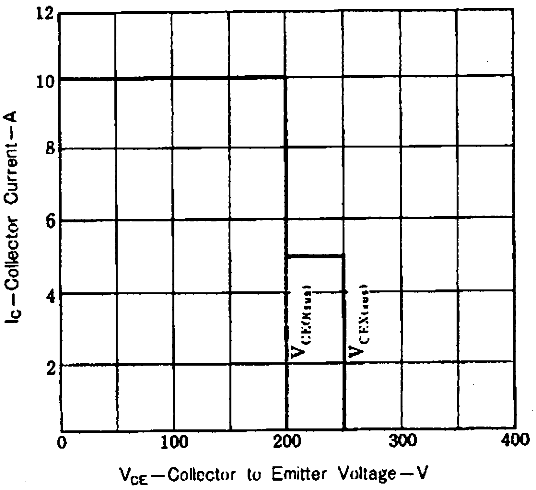
** PW ≦ 350 μs, duty cycle ≦ 2%

TABLE 1. – TEST CONDITIONS FOR DYNAMIC PERFORMANCE

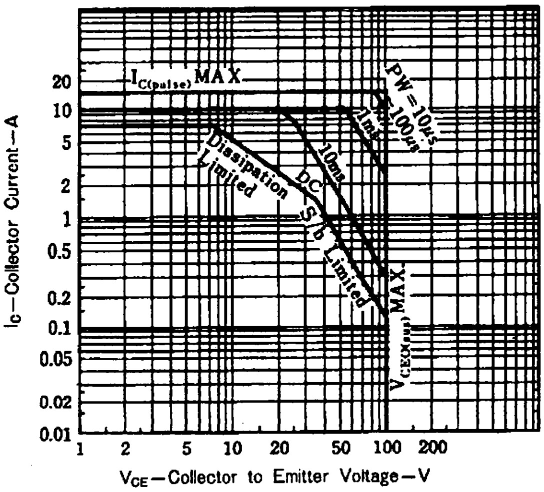
	VCEO (SUS)	VCEX (SUS)	ES/B	RESISTIVE SWITCHING
INPUT CONDITIONS	 PW Varied to Attain I_C = 5A	 PW Varied to Attain I_C = 5A duty cycle ≦ 2% Q_1 = 2SA969		
CIRCUIT VALUES	L_{coil} = 100μH, V_{CC} = 10V R_{coil} = 0.05Ω V_{clamp} (Unclamped)	L_{coil} = 180 μH, V_{CC} = 20V R_{coil} = 0.05Ω V_{clamp} = Rated V_{CEX} Value	L_{coil} = 40 μH, V_{CC} = 10V R_{coil} = 0.05Ω, R_{BB2} = 50Ω V_{clamp} (Unclamped)	R_L = 10Ω, V_{CC} ≃ 50V
TEST CIRCUITS	INDUCTIVE TEST CIRCUIT  D1 = F114F D2 = 6FH4S	OUTPUT WAVEFORM 	t_1 Adjust to Obtain IC $t_1 = \frac{L_{coil}(I_{C\,pk})}{V_{CC}}$ $t_2 = \frac{L_{coil}(I_{C\,pk})}{V_{clamp}}$	RESISTIVE TEST CIRCUIT 

TYPICAL CHARACTERISTICS (Ta=25°C)

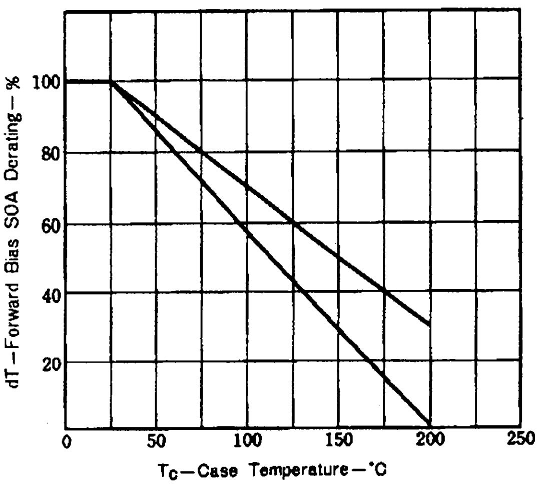
REVERSE BIAS SAFE OPERATING AREA



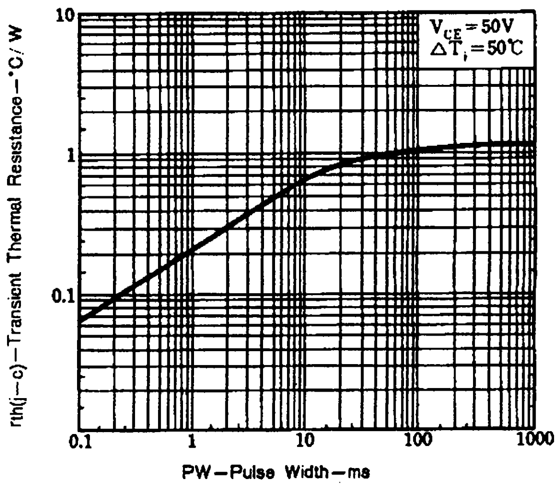
FORWARD BIAS SAFE OPERATING AREAS



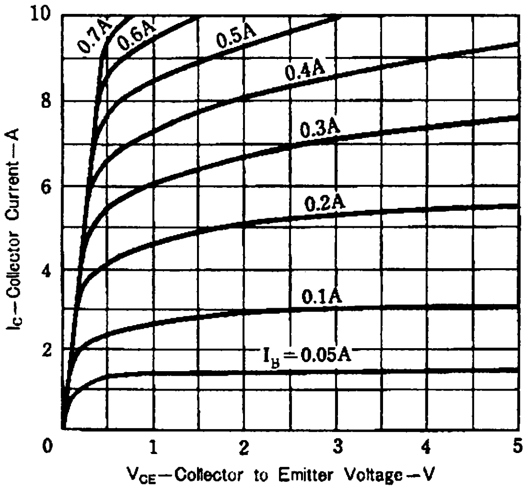
DERATING CURVE OF FORWARD BIAS SAFE OPERATING AREA



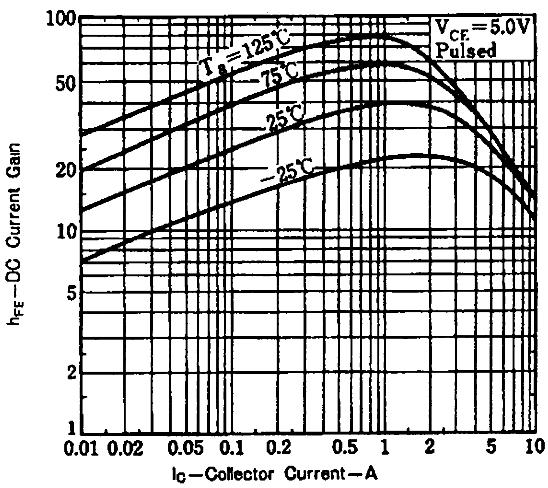
TRANSIENT THERMAL RESISTANCE



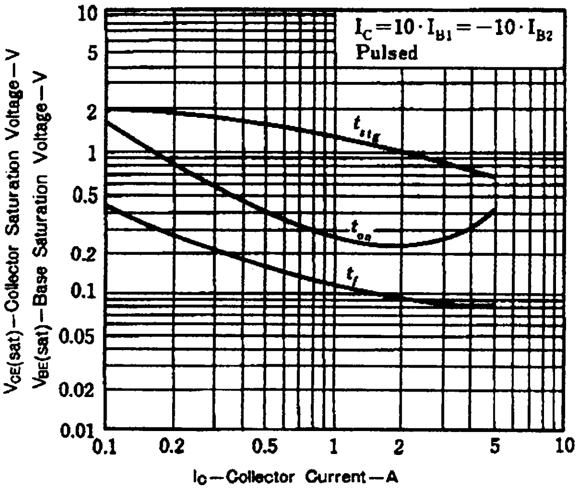
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



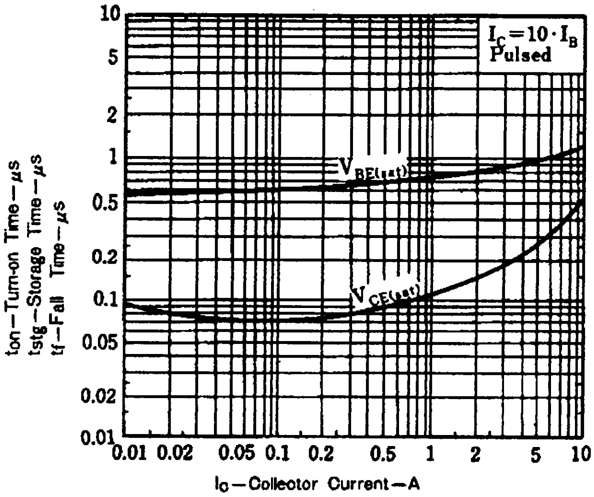
DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



TURN ON TIME, STORAGE TIME AND FALL TIME vs. COLLECTOR CURRENT



Nippon Electric Co.,Ltd.

NEC Building, 33-1, Shiba Gochome, Minato-ku, Tokyo 108, Japan
Tel; Tokyo 454—1111
Telex Address; NECTOK A J22686
Cable Address; MICROPHONE TOKYO

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